



# STS9013

NPN Silicon Transistor

## Descriptions

- General purpose application.
- Switching application.

## Features

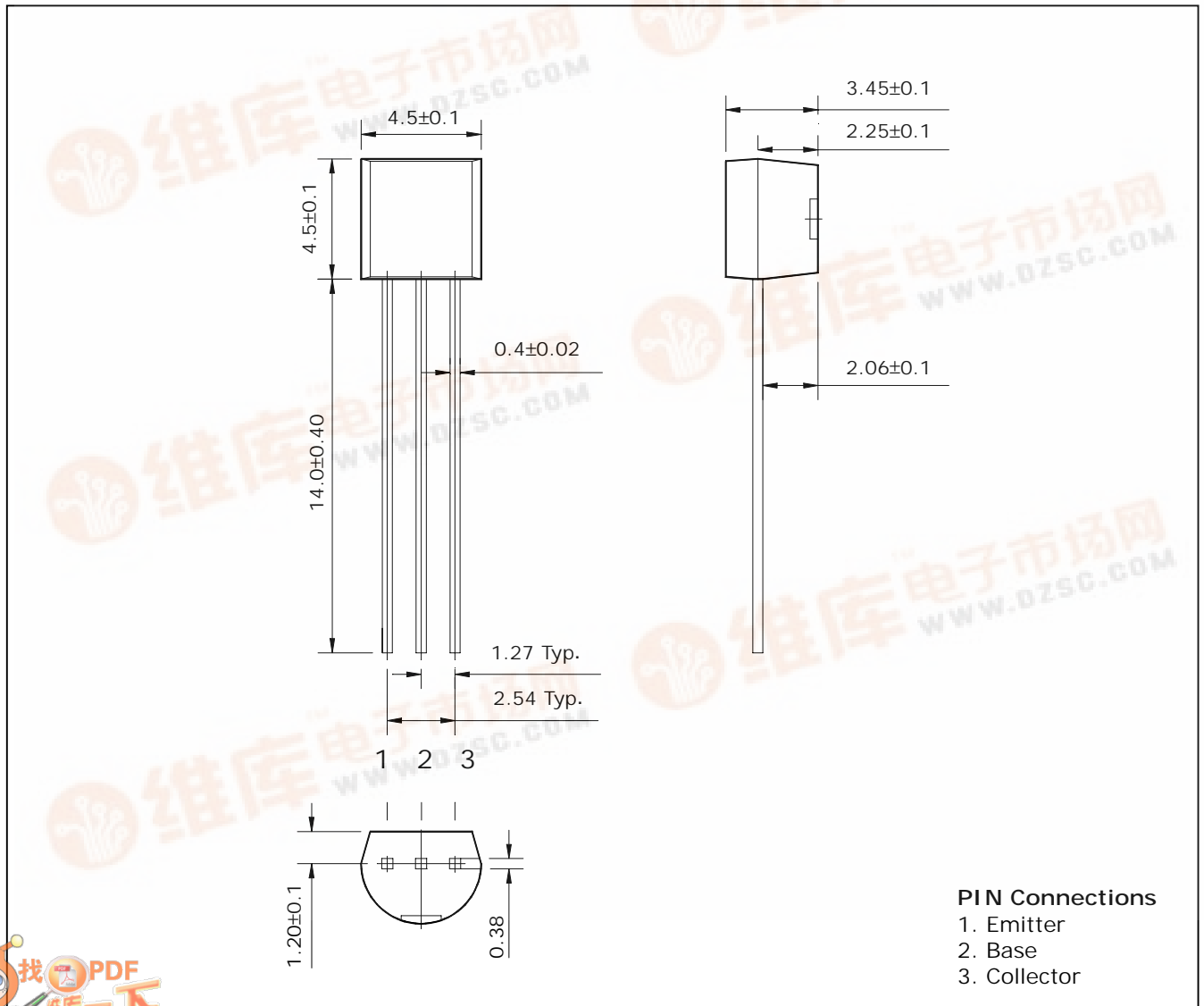
- Excellent  $h_{FE}$  linearity.
- Complementary pair with STS9012

## Ordering Information

Type NO.	Marking	Package Code
STS9013	STS9013	TO-92

## Outline Dimensions

unit : mm



## Absolute maximum ratings

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	$V_{CBO}$	40	V
Collector-Emitter voltage	$V_{CEO}$	30	V
Emitter-Base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	500	mA
Emitter current	$I_E$	-500	mA
Collector dissipation	$P_C$	625	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ 150	°C

## Electrical Characteristics

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB}=35, I_E=0$	-	-	0.1	μA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$	-	-	0.1	μA
DC current gain	$h_{FE}^*$	$V_{CE}=1V, I_C=50mA$	96	-	246	-
Collector-Emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$	-	0.1	0.25	V
Base-Emitter voltage	$V_{BE}$	$I_C=100mA, V_{CE}=1V$	-	0.8	1	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=20mA$	140	-	-	MHZ
Collector output capacitance	$C_{ob}$	$V_{CB}=6V, I_E=0, f=1MHz$	-	7.0	-	pF

\* :  $h_{FE}$  Rank / F : 96~135, G : 118~166, H : 144~202, I : 176~246.

Electrical Characteristic Curves

Fig. 1  $P_c - T_a$

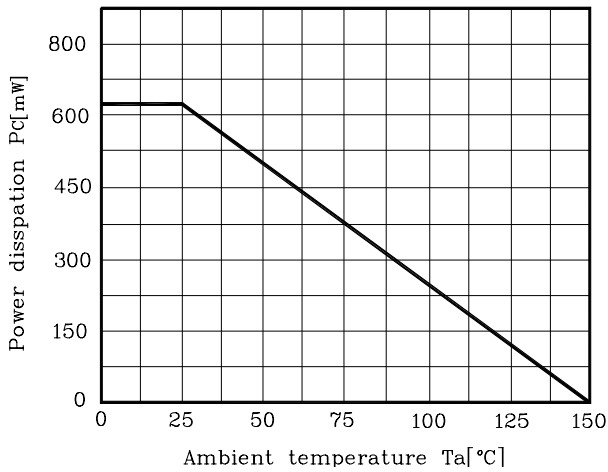


Fig. 2  $I_c - V_{BE}$

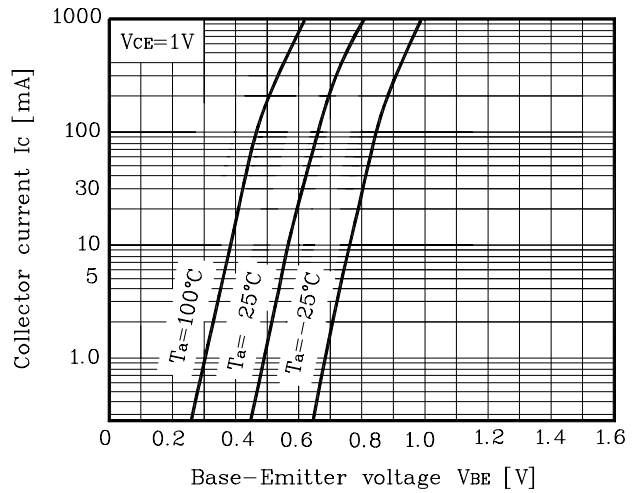


Fig. 3  $I_c - V_{CE}$

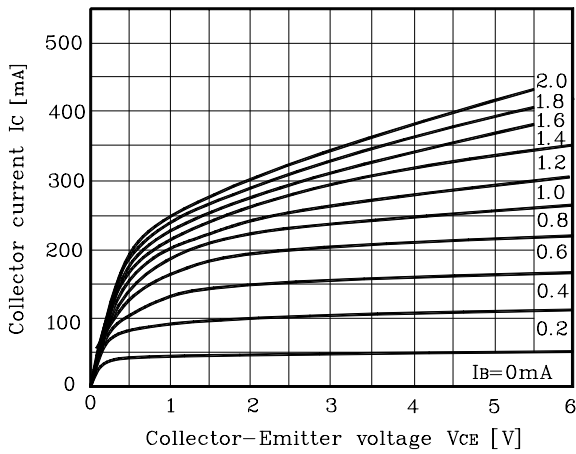


Fig. 4  $V_{CE(SAT)} - I_c$

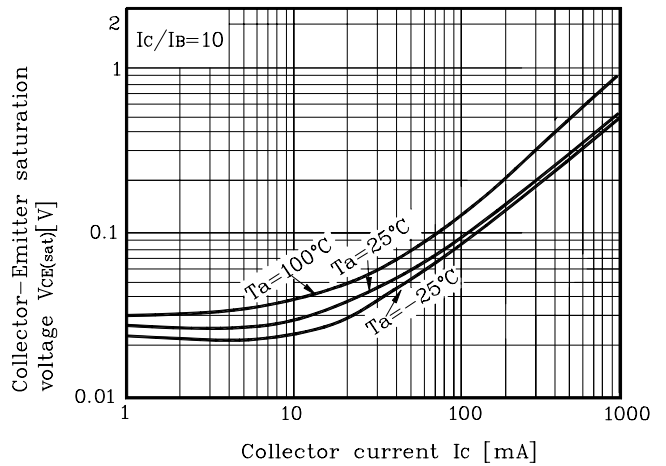


Fig. 5  $h_{FE} - I_c$

